

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a transistor, includes the steps of preparing a substrate, preparing a liquid material containing a silane compound, the silane compound forming a high order silane when photopolymerized, coating the liquid material on the substrate so as to form a coating film, exposing the coating film to an atmosphere comprising at least one of oxygen and ozone so as to oxidize a surface of the coating film, and performing at least one of thermal processing and photoirradiation processing on the coating film in an inert atmosphere so as to transform the coating film into a silicon layer and a silicon oxide layer disposed on the silicon layer.